





100V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- I_C = -2A High Continuous Current
- I_{CM} = -6A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -300mV @ -1A
- Complementary NPN Type: FZT653
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

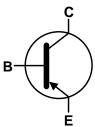
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

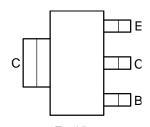
SOT223







Device Symbol



Top View Pin-Out

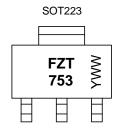
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT753TA	AEC-Q101	FZT753	7	12	1,000
FZT753QTA	Automotive	FZT753	7	12	1,000
FZT753TC	AEC-Q101	FZT753	13	12	4,000
FZT753QTC	Automotive	FZT753	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 753 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-2	Α
Peak Pulse Current	Ісм	-6	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0	W	
Power Dissipation	(Note 7)	Б	2.0		
Power Dissipation	(Note 8)	P_{D}	1.6	۷V	
	(Note 9)		1.2		
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{ hetaJA}$	78.1		
	(Note 9)		104	İ	
Thermal Resistance Junction to Lead (Note 10)		$R_{ heta JL}$	12.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 11)

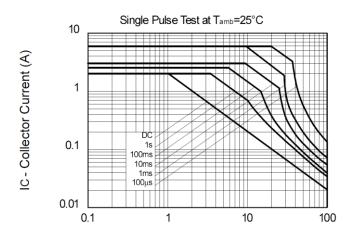
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- still air conditions whilst operating in a steady-state. 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 10. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

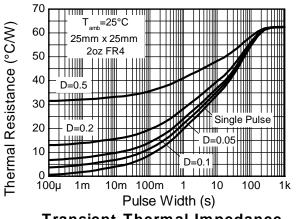


Thermal Characteristics and Derating Information

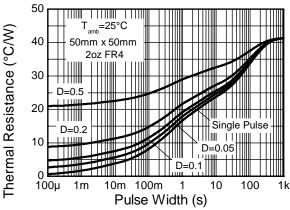


VCE - Collector Emitter Voltage (V)

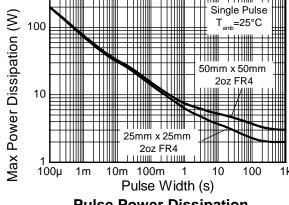
Safe Operating Area



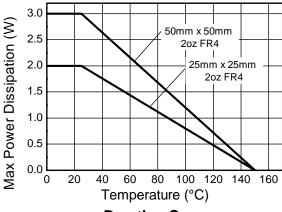
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-120	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-100	_	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100 \mu A$
Collector Cut-Off Current		_	<1	-100	nA	V _{CB} = -100V
Collector Cut-Oil Current	I _{CBO}	_	_	-10	μΑ	V _{CB} = -100V, T _A = +125°C
Emitter Cut-Off Current	I _{EBO}	_	<1	-100	nA	$V_{EB} = -5.6V$
Collector-Emitter Saturation Voltage (Note 12)	V	-	-0.17	-0.3	V	$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	_	-0.30	-0.5	V	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	_	-0.9	-1.25	V	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	_	-0.8	-1.0	V	$I_{C} = -1A$, $V_{CE} = -2V$
	hFE	70	200	_		$I_C = -50 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Coin (Note 12)		100	200	300		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 12)		55	170	_	_	$I_C = -1A$, $V_{CE} = -2V$
		25	55	_		I _C = -2A, V _{CE} = -2V
Current Gain-Bandwidth Product	f⊤	100	140	-	MHz	V _{CE} = -5V, I _C = -100mA f = 100MHz
Turn-On Time	t _{on}	_	40	_	ns	$V_{CC} = -10V, I_{C} = -500mA$
Turn-Off Time	t _{off}	_	600	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Output Capacitance	C _{obo}	_	_	30	pF	V _{CB} = -10V, f = 1MHz

Note:

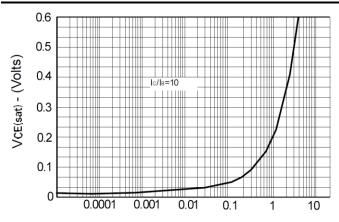
12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



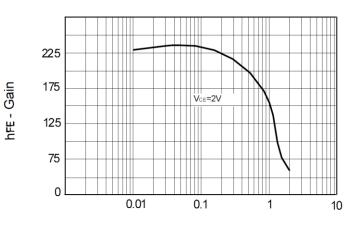
VBE - (Volts)

FZT753

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

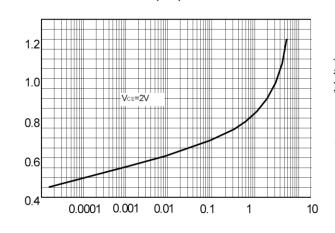


Ic - Collector Current (Amps)

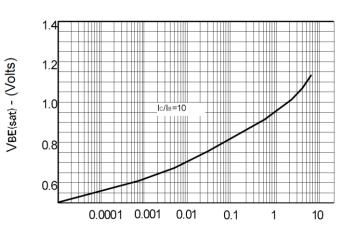


Ic - Collector Current (Amps) **hFE v IC**

VCE(sat) v IC

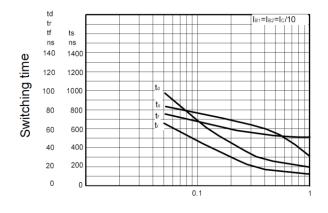


Ic - Collector Current (Amps)



Ic - Collector Current (Amps)

VBE(on) v IC



Ic - Collector Current (Amps)

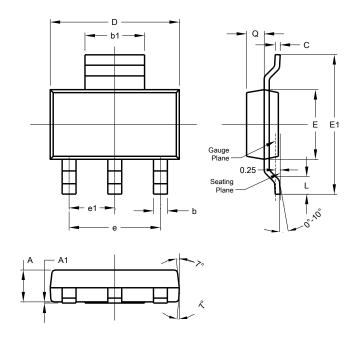
Switching Speeds

VBE(sat) v IC



Package Outline Dimensions

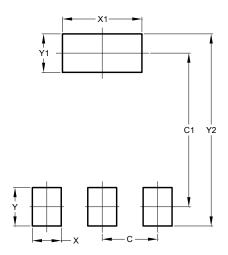
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
C2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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